



FORM PTO-1449				Atty. Docket No. XA-9721A		Appln. No. 10/786,334	
<u>LIST OF DOCUMENTS CITED BY APPLICANT</u>				Applicant Keisuke TSUKAMOTO et al.			
				Filing Date February 26, 2004		Group 2811	
				U.S. PATENT DOCUMENTS			
Examiner Initial		Document Number	Date	Name	Class	Sub-class	Filing Date
ca	AA	5,251,168	10/5/93	Chung et al.	365	51	
ca	AB	6,590,254	7/8/03	Tanaka (corrs. to Doc AL)	257	315	
ca	AC	5,946,320	8/31/99	Shimizu et al. (corrs. to Doc AM)	365	185.01	
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						
FOREIGN PATENT DOCUMENTS							
Examiner Initial		Document Number	Date	Country	Class	Sub-class	Translation
ca	AL	2001-332708	11/30/01	Japan			Abstract
ca	AM	11-97652	4/9/99	Japan			Abstract
ca	AN	11-284134	10/15/99	Japan			Abstract
ca	AO	11-54730	2/26/99	Japan			Abstract
ca	AP	11-265891	9/28/99	Japan			Abstract
ca	AQ	5-235366	9/10/93	Japan			Abstract
ca	AR	2-111075	4/24/90	Japan			Abstract
	AS						
OTHER (including author, title, date, pertinent pages, etc.)							
	AT						
Examiner 				Date Considered 4-14-05			
EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.							

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					Filing Date HEREWITH		Group	
U.S. PATENT DOCUMENTS								
Examiner Initial		Document Number	Date	Name	Class	Sub-class	Filing Date	
<i>on</i>	AA	5,946,230	8/99	Shimizu et al.	257	314		
	AB							
	AC							
	AD							
	AE							
	AF							
	AG							
	AH							
	AI							
FOREIGN PATENT DOCUMENTS								
Examiner Initial		Document Number	Date	Country	Class	Sub-class	Translation	
	AJ							
	AK							
	AL							
	AM							
	AN							
	AO							
OTHER (including author, title, date, pertinent pages, etc.)								
<i>ch</i>	AP	Kim et al., "A Novel 4.6F ² NOR Cell Technology With Lightly Doped Source (LDS) Junction For High Density Flash Memories," IEDM (International Electron Devices Meeting), 1998, pp. 979-982.						
	AQ							
Examiner <i>JEG</i>					Date Considered <i>4-14-05</i>			
EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.								